

Solutions in language processing

Multilingual access to Intellectual Property Information

Bernard Normier Langtech, Nov. 2003

>Lingway¢

- Products
 - Applications based on NLP
 - Knowledge management, text mining
 - > Vertical applications: Patents, Pharma

Customers and partners



























>Patent information: a very large technical corpus¢

- > 1 million new documents / year
 - > including 200,000 in Europe
- > 80% of technical information
 - > is published in patent documentation
- > 60,000 companies
 - >use patents in Europe

>User needs¢

> Get relevant patents in time

- > Critical information for technological and marketing watch
- > Time is essence of watch

> Typical flow = 500-1000 patents/month

- > Downloaded from patent databases
- > Need for « fast reading » tools
- > Don't miss the important information !

> Hide and seek game

- > Get a protection without being easily found
- > The important info is often hidden somewhere in the patent document (10 50 pages)



>New needs¢

- > Search by non-specialists in large companies
 - Not only Intellectual Property department, but directly Researchers, Engineers, Lawyers
 - > Free databases availables on Internet > EPO, USPTO, etc.
- > SMEs are new users
 - > With no expertize in Information management

>Patent databases¢

Indexed by the IPC

- > International classification of 60,000 entries
- > 14 levels depth
- > Very complex to use

> Multilingual corpus

- > First published in the language of the original national patent office
- > Delivery time for availability in other languages
- > In any case, not available in all languages

> Value added commercial offer

- > Abstracts manually rewritten and/or translated by experts
 - => delivery time and cost !

>lingway;

>NLP based solution¢

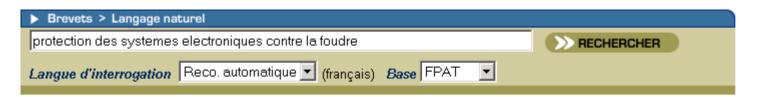
- > Multilingual search
 - > On external or internal servers
- > Categorization
 - > Send patents to the relevant experts in the company
- > Reading aids (micro-analysis)
 - > Summarization, vizualization, translation
- > Clutering, extraction (macro-analysis)
 - > Global vizualization tools

>Multilingual search¢

- > Based on a multi-layer dictionnary
 - > 3 levels inherited from Genelex Eagles model
 - > Generic ontology level with about 70.000 concepts
 - > Mappings between ontology and taxonomy (IPC)
- > Currently supporting X-IR between
 - > French, English, Spanish, German. Portuguese and Dutch under development
 - > Using the Connexor morphological tagger
- > Combining IPC and abstract search
 - > Query is categorized on IPC Query is translated in boolean search on abstracts
 - > Merging and ranking the 2 sets of results



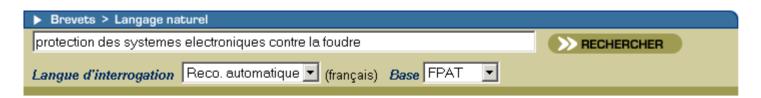


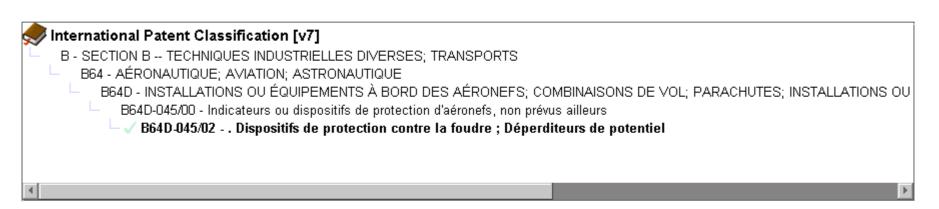














ADHESIVELY BONDED JOINTS IN CARBON FIBRE COMPOSITE STRUCTURES

BAE SYSTEMS plc / Warwick House, P.O. Box 87, Farnborough Aerospace Centre / Farnborough, Hampshire

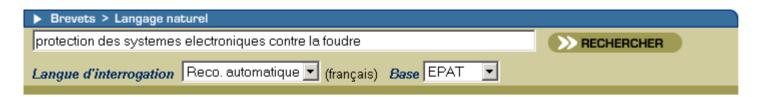
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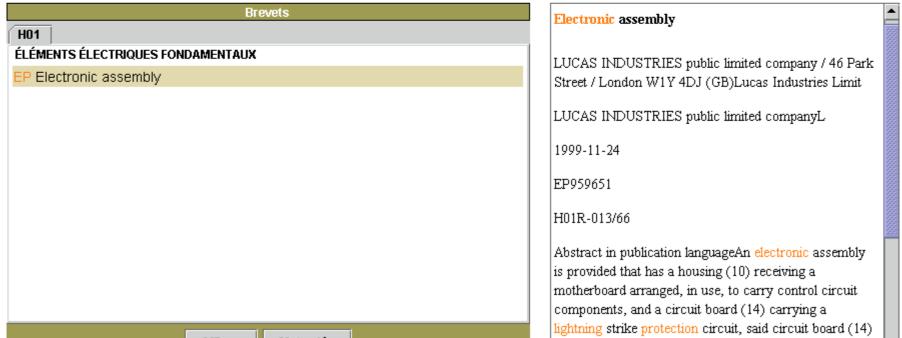
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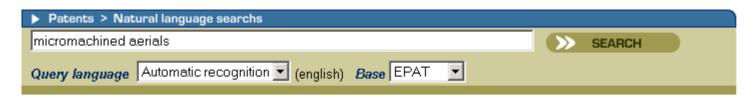


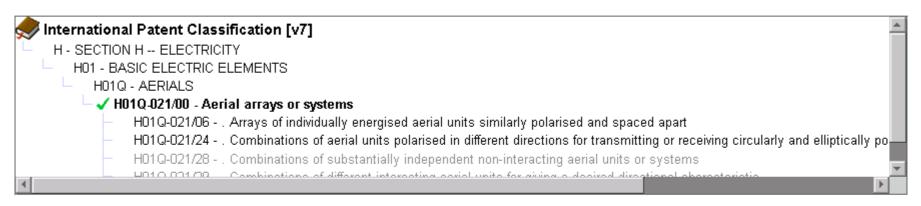


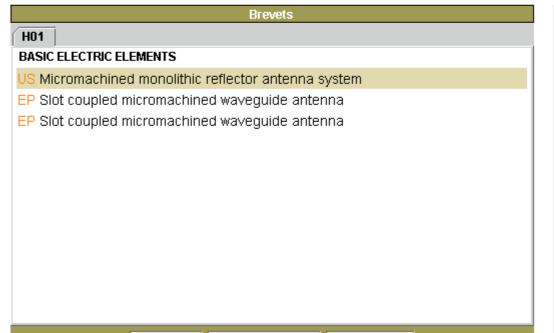






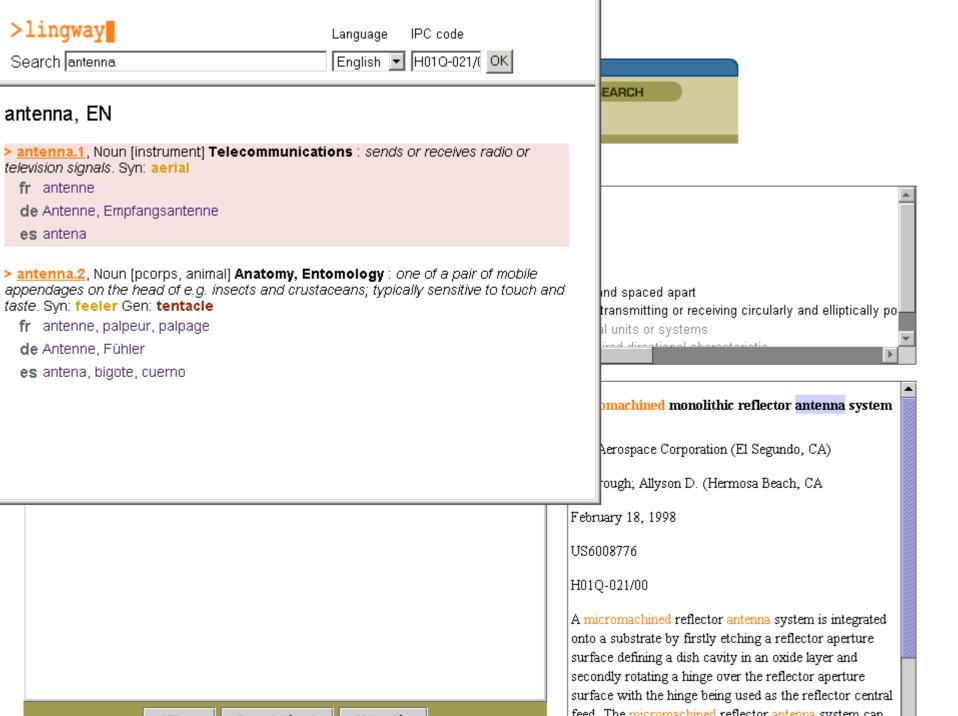






Micromachined monolithic reflector antenna system The Aerospace Corporation (El Segundo, CA) Yarbrough; Allyson D. (Hermosa Beach, CA February 18, 1998 US6008776 H01Q-021/00 A micromachined reflector antenna system is integrated onto a substrate by firstly etching a reflector aperture surface defining a dish cavity in an oxide layer and secondly rotating a hinge over the reflector aperture

surface with the hinge being used as the reflector central



> Reading aids (micro-analysis) ¢

- > Two features based on the same XML tagging
 - > Entity extraction:
 - > person names (+ their role)
 - > Company names, patent references, etc.
 - > Sentence identification
 - > Patent object, invention advantage, previous drawbacks, independant claims
- > Summarization
 - > A collection of selected entities and sentences
- > Visualization:
 - > Navigation in the document thru the XML tagging



Contents

- .. Abstract
- 2. References Cited [Referenced By]
- 3. Claims
- 4. Description
- 5. BACKGROUND OF THE INVENTION
- 6. SUMMARY OF THE INVENTION
- BRIEF DESCRIPTION OF THE DRAWINGS

Synthetic Views

- Person(s)
- Organization(s)
- Project(s)
- Patent(s)
- Concept(s)
- Patent Object(s)
- Previous patent Drawback(s)
- Improvement(s) / Advantage(s)

Person(s): 16 Occurences

Person	ΝЬ	Occurences
A.D. Yarbrough	1	> <u>1</u>
Cole; Robert C.	1	> <u>1</u>
<u>D. Rutledge</u>	1	> <u>1</u>
<u>Das</u>	1	> <u>1</u>
<u>Fletcher</u>	1	> <u>1</u>
<u>G. Rebeiz</u>	1	> <u>1</u>
K.S.J. Pister	1	> <u>1</u>
<u>Le; Hoanganh</u>	1	> <u>1</u>
Malos; Jennifer H.	1	> <u>1</u>
N.W. Judy	1	> <u>1</u>
Osofsky; Samuel S.	1	> <u>1</u>
R.S. Fearing	1	> <u>1</u>
Reid; Derrick Michael	1	> <u>1</u>
Robertson; Ruby E.	1	> <u>1</u>
S.R. Burgett	1	> <u>1</u>
Yarbrough: Alluson D	1	S1

Micromachined monolithic reflector antenna system

United States Patent: 6,008,776

(108 of 181)

United States Patent

6.008.776

Yarbrough , et al.

December 28, 1999

Micromachined monolithic reflector antenna system

Abstract

A micromachined reflector antenna system is integrated onto a substrate by firstly etching a reflector aperture surface defining a dish cavity in an oxide layer and secondly rotating a hinge over the reflector aperture surface with the hinge being used as the reflector central feed. The micromachined reflector antenna system can be made with an array of reflector antennas and integrated onto a single substrate with front end receiver circuits operating as a high frequency receiver on a chip with reduced size and cost and operating at hundreds of GHz.

Inventors:

<u>Yarbrough; Allyson D.</u> (Hermosa Beach, CA); <u>Osofsky; Samuel S.</u> (Torrance, CA); <u>Robertson; Ruby</u> E. (Los Angeles, CA); <u>Cole; Robert C.</u> (Rancho Palos Verdes, CA)

Assianee:

The Aerospace Corporation (El Segundo, CA)

Appl. No.:

surface with the hinge being used as the reflector central

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FIG. 1 depicts a microelectromechanical systems (MEMS) integrated receiver having both reflector antennas and front end receiver circuits integrated on a single substrate. FIGS. 2a-e are diagrams of a substrate to be processed to form a MEMS reflector on the substrate. DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENT An embodiment of the invention is described with reference to the figures using reference designations as shown in the figures. Referring to FIG. 1, a monolithic microwave integrated circuit 10 is an integrated receiver for use in communication systems. An embodiment of the invention is described with reference to the figures using reference designations as shown in the figures. Referring to FIG. 1, a monolithic microwave integrated circuit 10 is an integrated front end receiver circuit 13 through the network 11. The receiver circuit 13 is of a conventional design using conventional integrated semiconductor processes. The receiver circuit 13 comprises by way of example, a low noise amplifier 14, a band pass filter 14 providing a radio frequency RF signal to an another band pass filter 22 for down converting a received RF signal into an IF signal. The mixer 18 provides the IF signal to another band pass filter 24 which provides an intermediate frequency (IF) signal 26 as an output. The reflectors 12a-c are made using microelectromechanical systems (MEMS) processes and conventional semiconductor processes as more dearly depicted in FIGS. 2a-e. Referring to FIGS 2a-e. a MEMS reflector is preferably made upon a substrate 40 with a surface of appropriate crystalline orientation. The substrate may be bulk silicon. The substrate 40 with a surface of appropriate crystalline orientation. The substrate may be bulk silicon. The substrate 40 with a surface of appropriate crystalline orientation. The substrate may be bulk silicon. The substrate 40 with a surface of appropriate crystalline orientation. The substrate may be bulk silicon. The substrate 40 with a surface of appropriate crystalline orientation. Th				BRIEF DESCRIPTION OF THE DRAWINGS
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communications systems. It is desirable for communications satellites to use higher frequencies, to together to complete the avoid not only terrestrial microwave-link congestion and noise but also traffic from other users. antenna structure. There are also other considerable advantages, First, the beamwidth of an antenna narrows as the These components offer frequency increases, that is, the beamwidth of an antenna is inversely proportional to both the high-frequency operation antenna aperture and the frequency of transmission, so greater numbers of satellites can relay to but do not include a MEMS the same ground antenna without interfering with each other. Second, moving to higher frequencies reflector antenna having a also allows the use of smaller onboard satellite antennas, reducing weight. At millimeter-wave central feed suspended frequencies, electrically large but physically small antenna structures become feasible because of entirely above the plane of the short wavelengths involved. Finally, in the 2-4 GHz C-band, limits are imposed on radiated power to prevent interference with terrestrial microwave links. These limits either do not exist or are the cavity aperture, all on a single wafer. greatly relaxed at the higher frequencies. At frequencies much above C-band, the electronics in the receiver produce most of the noise that competes with the desired signal. However, at frequencies While MEMS processes can above 10 GHz, the atmospheric absorption of RF signals causes massive propagation losses. To release a structure to be overcome these losses, operation at higher, less-congested frequency regimes requires not only suspended, MEMS processes components that deliver much higher performance, but also highly sophisticated ground stations have not been applied to with larger antennas. Also, oxygen and water absorption resonances occur between 60 GHz and the manufacture of 125 GHz, providing opportunities for intersatellite communications that are virtually immune to integrated reflectors having interference or jamming from the ground. As components of sufficiently high performance are central feeds suspended developed and become available, it will be desirable to design satellites that take full advantage of above the plane of the these frequencies. A typical communications payload is one quarter of the dry mass of a satellite. cavity aperture on a single Applying micromachining technology to payloads can achieve significant savings in weight and cost. wafer. For example, a waveguide used for routing signal energy between and within subsystems, can be These and other integrated into the bulk substrate of a microwave integrated circuit, reducing the need for external disadvantages are solved or metal waveguide sections and combiners. Presently, the silicon or gallium arsenide substrate upon reduced using the invention. which microwave integrated circuits are fabricated provides a mechanical support for the active semiconductor layers and the metalization and may serve as a heat sink. Mobile systems and dynamic communication networks can be made more compact and versatile by micromachining and exploiting unused substrate volume. Personal communications systems increasingly require the use of lightweight, low-cost receivers. A large number of compact circuits of modest performance can be produced. Micromachining technology can meet the need for integrated subsystems by using Advantage(s) / Improvement(s): 2 Occurences semiconductor substrate material for multilevel and buried interconnects. The development of micromachining technology would allow inexpensive, batch-fabricated devices to be used in personal communication systems. Miniature horn and reflector antennas as well as arrays have been investigated and some have been fabricated with the use of available micromachining techniques. Confidence Advantage An integrated horn antenna for millimeter-wave applications has been suggested and a 802 GHz It is desirable for imaging array, double polarized antennas, monopulse antennas, and high-gain, step-profiled, communications satellites to diagonal-horn antennas have been proposed. The integrated horn antenna included a pyramidal use higher frequencies, to horn cavity at the bottom of which is a dipole antenna. The pyramidal horn cavity is fabricated on avoid not only terrestrial +++ one substrate, while the dipole antenna element is deposited on a thin membrane fabricated on a microwave-link congestion separate wafer. These two, and subsequent wafers required, are then carefully stacked, aligned and and noise but also traffic bonded or fused together to complete the antenna structure. These components offer highfrom other users. frequency operation but do not include a MEMS reflector antenna having a central feed suspended entirely above the plane of the cavity aperture, all on a single wafer. Additionally, as the frequency As components of sufficiently high of operation of a subsystem increases, packaging and interconnect schemes assume critical performance are developed importance. Often high performance can be achieved by advanced circuit designs which may be and become available, it will compromised by inefficient intrachip paths and packaging that leads to bottlenecks and losses. +++ Communication systems presently use discrete antennas and reflectors, which are interfaced to the be desirable to design front-end of receiver systems via waveguide, coaxial or planar interconnects. However, these satellites that take full advantage of these external connections to receiver circuits can inject noise into the received signal path, limiting the ability to distinguish low-level signals in the presence of noise. Reflectors and antennas typically frequencies. have central feeds suspended above the reflector. While MEMS processes can release a structure to be suspended, MEMS processes have not been applied to the manufacture of integrated reflectors having central feeds suspended above the plane of the cavity aperture on a single wafer. These and other disadvantages are solved or reduced using the invention.

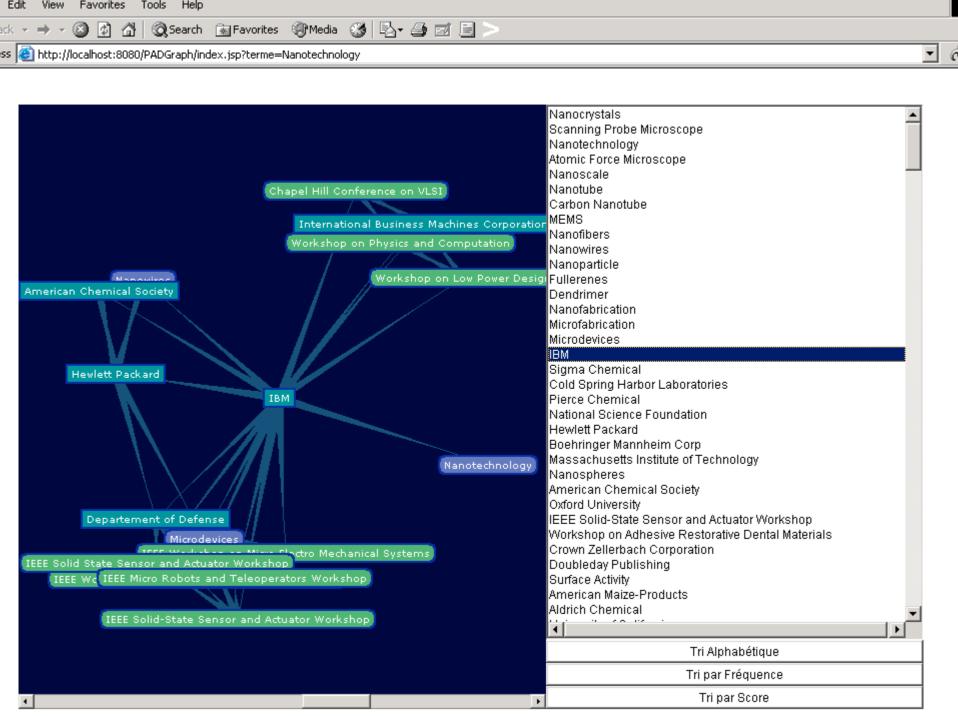
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> Clutering, extraction (macro-analysis) \$

- > Clustering of tagged entities
 - > Companies, workshops, inventors, technologies
- > Visualization:
 - > Graphs of co-occurrences
- > Expert tool for
 - > Technological watch
 - > Marketing watch

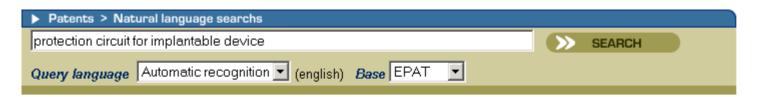


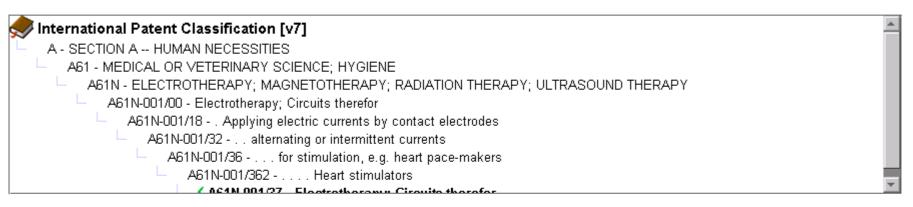
>Future developments¢

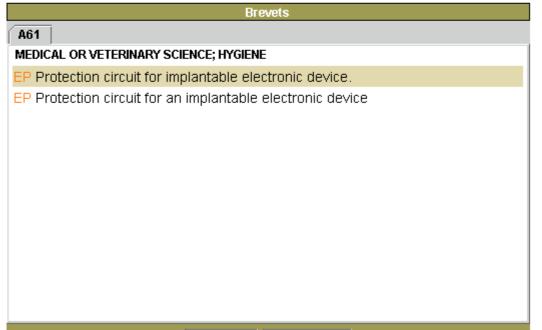
- > Title / abstract translation
 - > Reuse the patent dictionary for MT
 - > Interface with 3rd party MT engine for plain texts
- > Focused categorization
 - > Categorize on selected sentences only











Protection circuit for implantable electronic device.

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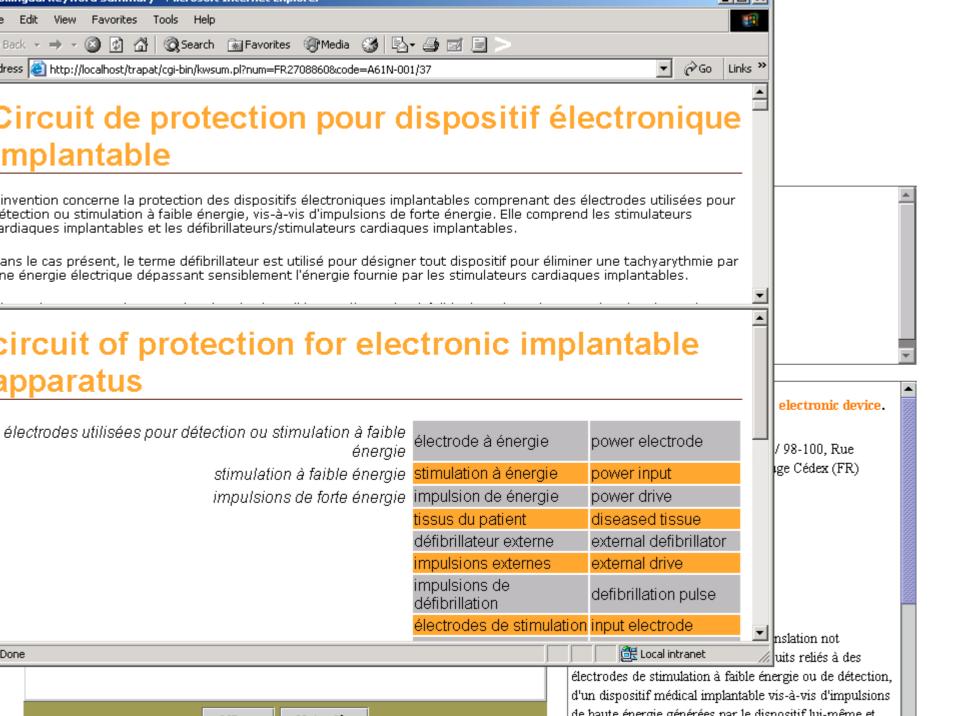
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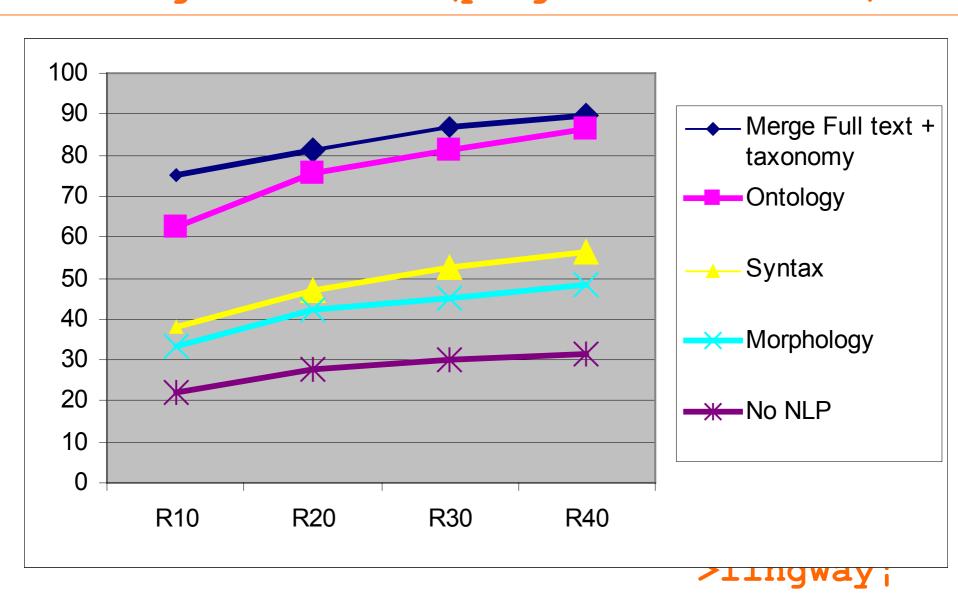
A61N-001/37

Abstract in publication language, translation not availableL'invention protège des circuits reliés à des électrodes de stimulation à faible énergie ou de détection, d'un dispositif médical implantable vis-à-vis d'impulsions

de houte énergie générées par le dispositif lui-même et



Apport des connaissances linguistiques Projet ePatent (programme eContent)



Thank you!